

Influence of the electric field on edge dislocations in smectics

by

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Abstract

The electric field applied perpendicularly to smectic layers breaks the rotational symmetry of the system. Consequently, the elastic energy associated with distortions induced by an edge dislocation diverges logarithmically with the size of the system. In freely suspended smectic films the dislocations in the absence of the electric field are located exactly in the middle of the film. The electric field, E , above a certain critical value, E_c , can shift them towards the surface. This critical field (in Gauss cgs units) is given by the following approximate formula $E_c = \sqrt{4\pi B(a\gamma/\sqrt{KB} - b)/(\epsilon_a(N - 2))}$. Here, B and K are smectic elastic constants, γ is the surface tension, N is the number of smectic layers and ϵ_a is the dielectric anisotropy. The constant $b = 0.85 \pm 0.07$ and $a = 1.45 \pm 0.01$. Additionally, we assumed that $\sqrt{K/B} = d$, where d is the smectic period. This formula is valid for $\gamma/\sqrt{KB} > 2$ and $N > 12$. For smaller values of the surface tension and large N the linear relation between E_c^2 and $\gamma/\sqrt{KB}$ breaks down, since eventually for $\gamma/\sqrt{KB} \rightarrow 1$ and $N \rightarrow \infty$, $E_c^2(N - 2)$ approaches 0. The equilibrium location of a dislocation in the smectic film, h_{eq} , equals $NdG(x)$, where $x = E^2/E_c^2$ and $G(x)$ is a function independent of the film thickness (for $N > 12$) and of the value of the surface tension. PACS numbers: 61.30.Jf, 61.72.Lk, 61.30.Gd, 61.30.Cz

I Introduction

The influence of electric field on nematic liquid crystals has been a subject of interest due to its application in display devices[1]. Also recently the influence of the electric field on ferroelectric smectic C*[2] liquid crystals has gained considerable attention, since these systems can be used as electrooptical switches[3]. The electric field can easily deform the director field in nematics, because of their dielectric anisotropy. In ferroelectric smectics the electric field applied parallel to smectic layers can easily deform the helical polarization pattern. Here we study the influence of electric field on layer deformations in smectic A liquid crystals. If a field is applied perpendicularly to the layers of smectic A with negative dielectric anisotropy ($\epsilon_a < 0$), it can destabilize their regular arrangement. For homeotropic samples bounded by surfaces with strong anchoring, the layers should undergo a transition to a periodically distorted state (Helfrich-Hurault instability [1]). This undulation instability has not been observed since anchoring is never strong enough to support it. The instability is thus preempted by other instabilities such as anchoring transitions and nucleation of confocal textures[4] or focal conics[5]. In this article we assume $\epsilon_a > 0$, to ensure the stability of the system and study the influence of the field on edge dislocations.

It is well known that the electric (or magnetic) field breaks the rotational symmetry of the system, suppresses Landau-Peierls instability and consequently restores the true long range order[1] in the smectic system. The latter fact has far reaching consequences for the defects. In ordinary solids the energy of an edge dislocation per unit length diverges logarithmically with the size of the system. In smectic A this energy is finite and independent of the system size. However, in the electric field, the smectic should behave like a true solid and consequently the edge dislocation energy should diverge with the system size. This effect has not been

studied so far. The question remains if the electric field effects in finite systems can be easily measured with moderate fields accessible in laboratories.

In freely suspended smectic liquid crystal films edge dislocations are stabilized in the middle of the film[6,7]. This effect is understandable since surface elastic energy is larger than the bulk elastic energy and thus edge dislocations are repelled from the limiting free surfaces (smectic-air interfaces)[8]. However, we can expect that in a sufficiently strong electric field (above a certain critical field) the equilibrium location of the edge dislocation may shift towards the surface. The rest of this paper is devoted to the study of this effect.

The paper is organized as follows. In section II we discuss the deformations induced by an edge dislocation in a bulk system subjected to an electric field. In section III we do the same calculations for a finite system bounded by two free surfaces. The equation for the equilibrium location of an edge dislocation within the film and a critical field are also derived in this section. The results are discussed in section IV.

II Bulk system

The elastic energy density of a weakly deformed smectic A liquid crystal in the electric field, E , along the z -axis (perpendicular to smectic layers), is given by the following equation[1]:

$$f_b = \frac{1}{2} \left(B \left(\frac{\partial u(\mathbf{r})}{\partial z} \right)^2 + \frac{\epsilon_a E^2}{8\pi} |\nabla_{\perp} u(\mathbf{r})|^2 + K (\Delta_{\perp} u(\mathbf{r}))^2 \right). \quad (2.1)$$

The vertical displacement in the system at point $\mathbf{r}$ is $u(\mathbf{r})$, K and B are the curvature and compressional elastic constants, ϵ_a is the dielectric anisotropy. We assume that $\epsilon_a > 0$. The total elastic energy,

$$F_b = \int d\mathbf{r} f_b \quad (2.2)$$

minimized with respect to u leads to the following equation for the distortions in the system:

$$-\frac{\partial^2 u}{\partial z^2} - f_e \Delta_{\perp} u + \lambda^2 \Delta_{\perp}^2 u = 0. \quad (2.3)$$

Here $f_e = \epsilon_a E^2 / (4\pi B)$ is a dimensionless constant and $\lambda = \sqrt{K/B}$ a microscopic length.

The elementary edge dislocation (of Burgers vector, b , equal to the layer thickness, d) located at $z = h$ and $x = 0$ is characterized by the following condition:

$$u(x, z = h^{\pm}) = \begin{cases} 0, & \text{if } x \leq 0; \\ \text{sgn}(z - h)d/2, & \text{if } x > 0. \end{cases} \quad (2.4)$$

The displacement u is a multivalued function in the $z = h$ plane. The equilibrium solution that satisfies Eq(2.3) and condition (2.4) and thus minimizes the elastic energy in the presence of the dislocation is as follows:

$$u_b(x, z) = \text{sgn}(z - h) \left(\frac{d}{4\pi} \int dq \exp(-a(q)|z - h|) \frac{\exp(iqx)}{i(q - i0^+)} \right), \quad (2.5)$$

where

$$a(q) = \sqrt{\lambda^2 q^4 + f_e q^2} \quad (2.6)$$

The elastic energy of the deformations induced by the dislocation can be conveniently written in the following form:

$$F_b = F_c + \frac{1}{2} B \int dx \frac{\partial u_b(x, z)}{\partial z} (u_b(x, z = h^-) - u_b(x, z = h^+)), \quad (2.7)$$

where the derivative is evaluated at $z = h$. Here F_c is the core energy. Inserting u_b into Eq(2.7) gives:

$$F_b = F_c + \frac{Bd^2}{4\pi} \int_{2\pi/L}^{2\pi/r_c} dq \frac{a(q)}{q^2} \quad (2.8)$$

Here r_c is the core size and L is the size of the system in the x direction (in calculations one introduces the cutoff in the q integral[9]). It is assumed that the

system is infinite in the z direction. For $E = 0$ we find the elastic energy ($L \gg r_c$),

$$F_b = F_c + \sqrt{KB}d^2/2r_c. \quad (2.9)$$

independent of L . However in the electric field, $E \neq 0$, the energy diverges logarithmically with the size L of the system. We find the following approximate form of F_b in this case:

$$F_b = F_c + \frac{Bd^2\sqrt{f_e}}{4\pi} \ln\left(\frac{\sqrt{f_e}L}{2\pi\lambda}\right) + \sqrt{KB}d^2/2r_c \left(1 - \frac{\sqrt{f_e}r_c}{2\pi\lambda}\right), \quad (2.10)$$

In fact it also means that edge dislocations should interact with long range potential even when placed in the same plane, when in the absence of the electric field their interactions vanish[9,10].

The same observations are valid if we set $L \rightarrow \infty$, but assume finite size D in the z direction. Then, the energy diverges logarithmically with D . However, in this case, we have to specify boundary conditions at the surfaces bounding the smectic. This is done in the next section.

III Dislocations in films

In a symmetric freely suspended smectic film of thickness D subjected to an electric field E the elastic energy for each of the bounding surfaces located at $z = \pm D/2$ reads as follows[6,8]:

$$F_s = \frac{1}{2} \int d\mathbf{r}_\perp \left(\gamma |\nabla_\perp u_s|^2 + \frac{\epsilon_a E^2 d}{8\pi} |\nabla_\perp u_s|^2 + K d (\Delta_\perp u_s)^2 \right). \quad (3.1)$$

Here $u_s = u(x, z = \pm D/2)$ is the displacement of surface layers. The fact that the curvature energy and the electric energy are not only included in the bulk term but also in the surface term, follows from the comparison of the distortion energy in the discrete and continuous representation. In the discrete representation the layers have indices $i = 0, 1, 2, \dots$ and $u(x, z) = u_i(x)$. Then the curvature and electric

terms appear naturally for every layer including the surface one. In the discrete representation we sum over i instead of integrating over z and consequently for each layer, including the surface one, the electric term and the curvature term are multiplied by the smectic period d . Although for freely suspended films these terms can be neglected in comparison to the surface term[6-8], nonetheless in systems characterized by small surface tension they are by no means negligible [11]. That is why we shall keep them, although we notice that their influence on the calculated quantities is rather small for the systems considered in this paper. In particular for large D and large surface tension γ one could use the following simple and well known surface energy:

$$F_s = \frac{1}{2} \int d\mathbf{r}_\perp \gamma |\nabla u_s|^2. \quad (3.2)$$

without considerable change of results. At the end we shall discuss the differences between the results obtained from Eq(3.1) and those from Eq(3.2).

The minimization of $F_b + F_s$ (using Eq(3.1)) leads to Eq(2.3) in the bulk and the following boundary conditions:

$$-B \frac{\partial u}{\partial z} - \left(\gamma + \frac{\epsilon_a E^2 d}{4\pi} \right) \frac{\partial^2 u(x, z = -D/2)}{\partial x^2} + Kd \frac{\partial^4 u(x, z = -D/2)}{\partial x^4} = 0 \quad (3.3)$$

at $z = -D/2$ and

$$B \frac{\partial u}{\partial z} - \left(\gamma + \frac{\epsilon_a E^2 d}{4\pi} \right) \frac{\partial^2 u(x, z = D/2)}{\partial x^2} + Kd \frac{\partial^4 u(x, z = D/2)}{\partial x^4} = 0 \quad (3.4)$$

at $z = D/2$. The solution satisfying Eqs(2.3,3.3,3.4) and condition (2.4) is as follows:

$$u(x, z) = u_b(x, z) + u_p(x, z) \quad (3.5)$$

where u_b is given by Eq(2.5) and

$$u_p(x, z) = \frac{d}{4\pi} \int dq \frac{\exp(iqx)}{iq} (\exp(-a(q)z) f_1(q) + \exp(a(q)z) f_2(q)). \quad (3.6)$$

The function $a(q)$ is defined by Eq(2.6),

$$f_1(q) = \frac{a_1(q)(a_2(q)e^{a(q)(D+h)} + a_1(q)e^{-a(q)h})}{a_2(q)^2 e^{2a(q)D} - a_1(q)^2}, \quad (3.7)$$

$$f_2(q) = -\frac{a_1(q)(a_2(q)e^{a(q)(D-h)} + a_1(q)e^{a(q)h})}{a_2(q)^2 e^{2a(q)D} - a_1(q)^2}, \quad (3.8)$$

and

$$a_1(q) = \left(\gamma + \frac{\epsilon_a E^2 d}{4\pi} \right) q^2 + K dq^4 - Ba(q), \quad (3.9)$$

$$a_2(q) = \left(\gamma + \frac{\epsilon_a E^2 d}{4\pi} \right) q^2 + K dq^4 + Ba(q). \quad (3.10)$$

The energy associated with distortions induced in the smectic film of thickness D by the dislocation located at distance h from the center of the film is given by:

$$F(h) = F_b + \frac{1}{2}B \int dx \frac{\partial u_p(x, z)}{\partial z} (u_b(x, z = h^-) - u_b(x, z = h^+)), \quad (3.11)$$

which for finite D is finite, but which in the large D limit diverges as $\ln(D)$. The equilibrium location of the dislocation is determined by the minimum of $F(h)$ as a function of h i.e. by the solution of the following equation:

$$\int_0^\infty dq \left(\frac{a(q)}{q} \right)^2 \frac{a_1(q)a_2(q)e^{a(q)D} \sinh(2a(q)h)}{a_2(q)^2 e^{2a(q)D} - a_1(q)^2} = 0. \quad (3.12)$$

For $\gamma > \sqrt{KB}$ and small electric field E the dislocation is located exactly in the middle of the film at $h = 0$. However above a certain critical value of the electric field, E_c , the minimum at $h = 0$ becomes unstable and the dislocation moves out of the center of the film. The condition which determines the critical field is given by the following equation:

$$\int_0^\infty dq \left(\frac{a(q)}{q} \right)^2 \frac{a_1(q)a_2(q)e^{a(q)D} a(q)}{a_2(q)^2 e^{2a(q)D} - a_1(q)^2} = 0, \quad (3.13)$$

which corresponds to the vanishing of the second derivative of $F(h)$ with respect to h at $h = 0$. The solution of Eq(3.13) for the value of the critical field and of

Eq(3.12) for the equilibrium location of the dislocation in the film h_{eq} are discussed in the next section.

IV Results and discussion

The electric term has the same formal structure as the surface tension term. Consequently, since the location of the dislocation in the film depends on the competition between surface and bulk terms, we can expect that when the electric term multiplied by the size of the film is roughly proportional to the surface term, the dislocation will move from the middle of the film towards the surface. This condition can be simply written as follows:

$$\frac{\epsilon_a E_c^2}{4\pi} D \sim \gamma \quad (4.1)$$

Indeed, we find the following relation between the critical field E_c and the surface tension (assuming that the microscopic length, λ , is equal to d):

$$\frac{\epsilon_a E_c^2}{4\pi B} (N - 2) \approx a \frac{\gamma}{\sqrt{KB}} - b, \quad (4.2)$$

Here, $N = D/d$ is the number of smectic layers; $a \approx 1.45 \pm 0.01$ and $b \approx 0.85 \pm 0.07$ are two constants. This approximate formula works very well for $\gamma > 2\sqrt{KB}$ and $N > 12$. The difference between this approximate formula and numerical solution of Eq(3.13) is within few percents. In fact for typical experimental samples of thickness $1\mu\text{m}$ ($N \approx 300$), with $\gamma \approx 5\sqrt{KB}$, this difference is smaller than one percent.

For large N and $\gamma \rightarrow \sqrt{KB}$, $E_c^2(N - 2)$ approaches 0 and the linear relation (4.2) breaks down. In Fig.1 the critical field, $E_c^2(N - 2)\epsilon_a/(4\pi B)$, is plotted versus $\gamma/\sqrt{KB}$ for $N = 12$ and $N = 102$ for $\gamma/\sqrt{KB} \leq 2$. As γ increases the differences between the two cases decreases. Practically for $N \rightarrow \infty$, $E_c^2(N - 2)\epsilon_a/(4\pi B)$, should follow the same curve as for $N = 102$ except in the very small region close to $\gamma/\sqrt{KB} = 1$.

We can estimate the value of the critical field for typical liquid crystal sample characterized by large ϵ_a e.g. cyanobiphenyl. For $\epsilon_a = 10$ [12], $\gamma/\sqrt{KB} = 5$ [13] (in some lamellar systems of polymers it can be as large as 30 [14]), $N = 300$ and $B = 10^7$ dyn/cm² we find

$$E_c \approx 15\text{V}/\mu\text{m} \quad (4.3)$$

Such fields are easily obtained in typical experiments [15] and thus the influence of the electric field on an edge dislocation inside the film should be visible in experiments. Without the field two dislocations located in the center of the film could not cross easily. On the other hand, in the electric field, two dislocations located close to different surfaces can cross easily, which should be visible under the microscope.

Using the simplified surface elastic energy Eq(3.2) (instead of (3.1)) we find a formula similar to (4.2), where instead of $N-2$ there is N . However for $\gamma/\sqrt{KB} \leq 2$, the differences are much larger. In particular for $\gamma/\sqrt{KB} \rightarrow 1$, $E_c 2(N-2) \rightarrow 0$ independently of the film thickness.

Finally, we calculate the equilibrium location of the dislocation, h_{eq} , in the film. For $E < E_c$ we have $h_{eq} = 0$, while for $E \geq E_c$ we find the following relation between the electric field and h_{eq} :

$$h_{eq} = \pm NdG \left(\frac{E^2}{E_c^2} \right). \quad (4.4)$$

The function G , shown in Fig.2, is independent of the film thickness and the surface tension. It rises steeply for $E \geq E_c$, which means that for E even slightly above the critical field dislocations move far away from the middle of the film. For large electric fields the dislocations approach the surface i.e. $h_{eq} \rightarrow (D/2 - d)$. Since the function G is very flat for large values of E , thus for practical reasons, it should be very hard to shift the dislocation exactly at the surface by using the electric field only.

Another question of practical interest is to know whether the dislocation can easily reach its new equilibrium position after the electric field is applied, since there is in the system a kinetic barrier, known as Peierls-Nabarro stress, opposing the motion of the dislocation in the direction perpendicular to the layers. Thus, in order to move the dislocation, the glide force, F_g , acting on the dislocation must be comparable or larger than the Peierls-Nabarro force, $F_{P.N.}$, pinning the dislocation in its Peierls valley. The latter has been calculated by Lejcek[16]:

$$F_{P.N.} = \frac{3}{4} B b \sqrt{\frac{\pi \lambda}{r_c}} \exp\left(-\frac{2\pi r_c}{b}\right). \quad (4.5)$$

It strongly depends on the size of the dislocation core r_c , which at low temperature is of the order of d , but should be larger than d near a nematic-smectic phase transition. The glide force in our case equals

$$F_g = \left| \frac{\partial F(h)}{\partial h} \right| \quad (4.6)$$

This force vanishes for $h = 0$ and $h = h_{eq}$ and passes through the maximal value, F_g^{max} , in between. For $E \sim 3E_c$ and $N = 102$ we find

$$F_g^{max} \approx 0.01 \frac{Bd}{2\pi} \quad (4.7)$$

From Eq(4.6) and (4.7) we find that for $r_c = d$

$$F_{P.N.} \gg F_g^{max}, \quad (4.8)$$

but for $r_c \geq 2d$

$$F_{P.N.} \ll F_g^{max} \quad (4.9)$$

Consequently, we can expect that the phenomena studied here can be easily observed near a second order (or weakly first order) nematic-smectic phase transition when

the core of the dislocation is probably dissociated (Eq(4.9)). Otherwise, dislocations should be strongly pinned in the middle of the film (Eq(4.8)).

Although our results are not applicable for the case of negative anisotropy we can see that in such systems the dislocations would be favored by the electric field, applied perpendicular to layers. It opens an interesting problem of the nucleation of dislocations in such systems subjected to the electric field. It is known for example that for the ferroelectric liquid crystals the film can assume a cone configuration with the stable pore running through the film[17]. Similarly in our system the dislocation loops could be stabilized by the electric field.

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Figure Captions

Fig.1 $\epsilon_a E_c^2 (N - 2) / (4\pi B)$ versus $\gamma / \sqrt{KB}$ for $N = 12$ (dashed line) and $N = 102$ (solid line). Here E_c is the critical field, γ – surface tension and N – number of smectic layers.

Fig.2 The equilibrium location of the dislocation, h_{eq}/D , versus E^2/E_c^2 . Here E is the electric field, E_c – critical field, and D – thickness of the film. $h_{eq}/D=0$ corresponds to the middle of the film and $h_{eq}/D=0.5$ to the surface.